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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	75264
Total RAM Bits	516096
Number of I/O	341
Number of Gates	300000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1agle3000v2-fgg484

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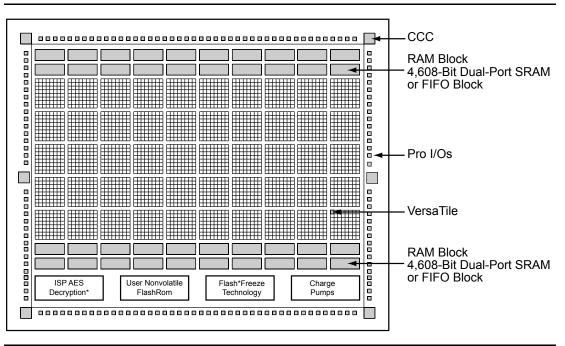


Figure 1-1 • IGLOOe Device Architecture Overview

Flash*Freeze Technology

The IGLOOe device has an ultra-low power static mode, called Flash*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash*Freeze technology enables the user to quickly (within 1 μ s) enter and exit Flash*Freeze mode by activating the Flash*Freeze pin while all power supplies are kept at their original values. In addition, I/Os and global I/Os can still be driven and can be toggling without impact on power consumption, clocks can still be driven or can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and states. I/O states are tristated during Flash*Freeze mode or can be set to a certain state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL in this mode.

Flash*Freeze technology allows the user to switch to active mode on demand, thus simplifying the power management of the device.

The Flash*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. It is also possible to use the Flash*Freeze pin as a regular I/O if Flash*Freeze mode usage is not planned, which is advantageous because of the inherent low power static and dynamic capabilities of the IGLOOe device. Refer to Figure 1-2 for an illustration of entering/exiting Flash*Freeze mode.

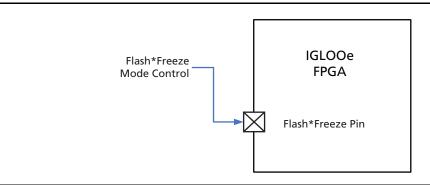


Figure 1-2 • IGLOOe Flash*Freeze Mode



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JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper powerup behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V \pm 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOOe FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

- 1. Core
- 2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

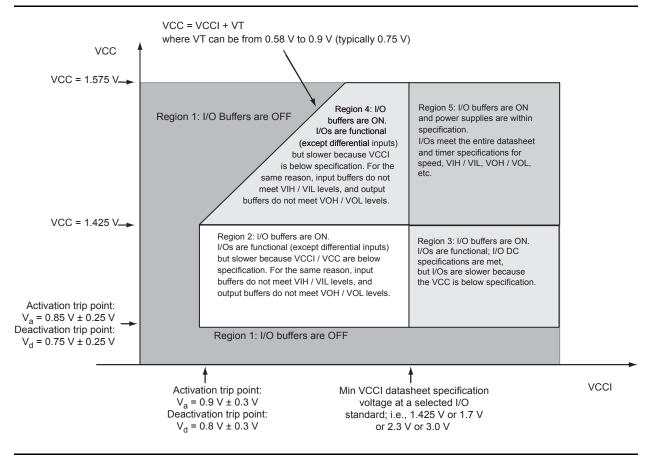


Figure 2-1 • V5 – I/O State as a Function of VCCI and VCC Voltage Levels

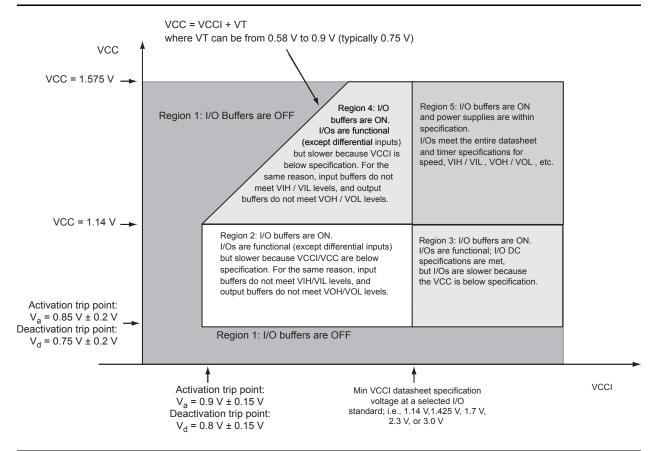


Figure 2-2 • V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels

Thermal Characteristics

Introduction

The temperature variable in Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J$$
 = Junction Temperature = ΔT + T_A

where:

T_A = Ambient Temperature

 ΔT = Temperature gradient between junction (silicon) and ambient ΔT = θ_{ia} * P

 θ_{ia} = Junction-to-ambient of the package. θ_{ia} numbers are located in Table 2-5.

P = Power dissipation

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IGLOOe DC and Switching Characteristics

Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹

	C _{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTL/LVCMOS	5	3.3	-	148.00
3.3 V LVCMOS Wide Range ⁴	5	3.3	-	148.00
2.5 V LVCMOS	5	2.5	-	83.23
1.8 V LVCMOS	5	1.8	-	54.58
1.5 V LVCMOS (JESD8-11)	5	1.5	-	37.05
1.2 V LVCMOS (JESD8-11)	5	1.2	-	17.94
1.2 V LVCMOS (JESD8-11) - Wide Range				17.94
3.3 V PCI	10	3.3	-	204.61
3.3 V PCI-X	10	3.3	-	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	-	24.08
2.5 V GTL	10	2.5	-	13.52
3.3 V GTL+	10	3.3	-	24.10
2.5 V GTL+	10	2.5	-	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.18
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60
SSTL3 (I)	30	3.3	26.02	114.67
SSTL3 (II)	30	3.3	42.21	131.69
Differential			•	•
LVDS	_	2.5	7.70	89.62
LVPECL	_	3.3	19.42	167.86

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.

2. PDC7 is the static power (where applicable) measured on VCCI.

3. PAC10 is the total dynamic power measured on VCCI.

4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.

1.2 V DC Core Voltage

Table 2-44 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
100 µA	4 mA	Std.	1.55	8.14	0.26	1.66	2.14	1.10	8.14	6.46	3.80	3.79	13.93	12.25	ns
100 µA	8 mA	Std.	1.55	6.68	0.26	1.66	2.14	1.10	6.68	5.57	4.25	4.69	12.47	11.36	ns
100 µA	12 mA	Std.	1.55	5.65	0.26	1.66	2.14	1.10	5.65	4.91	4.55	5.25	11.44	10.69	ns
100 µA	16 mA	Std.	1.55	5.36	0.26	1.66	2.14	1.10	5.36	4.76	4.61	5.41	11.14	10.55	ns
100 µA	24 mA	Std.	1.55	5.20	0.26	1.66	2.14	1.10	5.20	4.78	4.69	6.00	10.99	10.56	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \ \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-45 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{z∟}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
100 µA	4 mA	Std.	1.55	4.65	0.26	1.66	2.14	110	4.65	3.64	3.80	4.00	10.44	9.43	ns
100 µA	8 mA	Std.	1.55	3.85	0.26	1.66	2.14	1.10	3.85	2.99	4.25	4.91	9.64	8.77	ns
100 µA	12 mA	Std.	1.55	3.40	0.26	1.66	2.14	1.10	3.40	2.68	4.55	5.49	9.19	8.46	ns
100 µA	16 mA	Std.	1.55	3.33	0.26	1.66	2.14	1.10	3.33	2.62	4.62	5.65	9.11	8.41	ns
100 µA	24 mA	Std.	1.55	3.36	0.26	1.66	2.14	1.10	3.36	2.54	4.71	6.24	9.15	8.32	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

3. Software default selection highlighted in gray.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-48 • 2.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Unit s
4 mA	Std.	0.97	5.55	0.18	1.31	1.41	0.66	5.66	4.75	2.28	1.96	9.26	8.34	ns
8 mA	Std.	0.97	4.58	0.18	1.31	1.41	0.66	4.67	4.07	2.58	2.53	8.27	7.66	ns
12 mA	Std.	0.97	3.89	0.18	1.31	1.41	0.66	3.97	3.58	2.78	2.91	7.56	7.17	ns
16 mA	Std.	0.97	3.68	0.18	1.31	1.41	0.66	3.75	3.47	2.82	3.01	7.35	7.06	ns
24 mA	Std.	0.97	3.59	0.18	1.31	1.41	0.66	3.66	3.48	2.88	3.37	7.26	7.08	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-49 • 2.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Unit s
4 mA	Std.	0.97	2.94	0.18	1.31	1.41	0.66	3.00	2.68	2.28	2.03	6.60	6.27	ns
8 mA	Std.	0.97	2.45	0.18	1.31	1.41	0.66	2.50	2.12	2.58	2.62	6.10	5.72	ns
12 mA	Std.	0.97	2.15	0.18	1.31	1.41	0.66	2.20	1.85	2.78	2.98	5.80	5.45	ns
16 mA	Std.	0.97	2.10	0.18	1.31	1.41	0.66	2.15	1.80	2.82	3.08	5.75	5.40	ns
24 mA	Std.	0.97	2.11	0.18	1.31	1.41	0.66	2.16	1.74	2.88	3.47	5.75	5.33	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.8 V LVCMOS

Low-Voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

1.8 V LVCMOS		VIL	VIH		VOL	VOH	IOL	юн	IOSH	IOSL	IIL¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	2	2	9	11	10	10
4 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	4	4	17	22	10	10
6 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	6	6	35	44	10	10
8 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	8	8	45	51	10	10
12 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI - 0.45	12	12	91	74	10	10
16 mA	-0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	16	16	91	74	10	10

Table 2-52 • Minimum and Maximum DC Input and Output Levels

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Software default selection highlighted in gray.

Test Point
Datapath
$$\downarrow$$
 35 pF $R = 1 k$
 $R = 1 k$
Test Point \downarrow
 $R to VCCI for t_{LZ} / t_{ZL} / t_{ZLS}$
 $R to GND for t_{HZ} / t_{ZH} / t_{ZHS}$
 $5 pF for t_{ZH} / t_{ZHS} / t_{ZL} / t_{ZLS}$
 $5 pF for t_{HZ} / t_{ZH} / t_{ZLS}$

Figure 2-9 • AC Loading

Table 2-53 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	1.8	0.9	_	5

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

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IGLOOe DC and Switching Characteristics

Timing Characteristics

1.5 V DC Core Voltage

Table 2-75 • 3.3 V GTL – Applies to 1.5 V DC Core VoltageCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V,Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	0.98	1.83	0.19	2.41	0.67	1.84	1.83			5.47	5.46	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-76 • 3.3 V GTL – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	1.55	2.09	0.26	2.75	1.10	2.10	2.09			7.91	7.89	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). IGLOOe devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

HSTL Class II		VIL	VIH		VOL	VOH	IOL	юн	IOSH	IOSL	IIL¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
15 mA ⁵	-0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15	66	55	10	10

Table 2-93 • Minimum and Maximum DC Input and Output Levels

Notes:

1. IIL is the input leakage current per I/O pin over recommended operating conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.

3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

4. Currents are measured at 85°C junction temperature.

5. Output drive strength is below JEDEC specification.

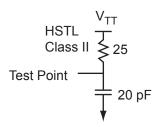


Figure 2-18 • AC Loading

Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-95 •HSTL Class II – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
Std.	0.98	2.62	0.19	1.77	0.67	2.66	2.40			6.29	6.03	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-96 • HSTL Class II – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{zH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{zHS}	Units
Std.	1.55	2.93	0.26	1.94	1.10	2.98	2.75			8.79	8.55	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Differential I/O Characteristics

Physical Implementation

Configuration of the I/O modules as a differential pair is handled by the Microsemi Designer software when the user instantiates a differential I/O macro in the design.

Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and DDR. However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-23. The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, IGLOOe also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).

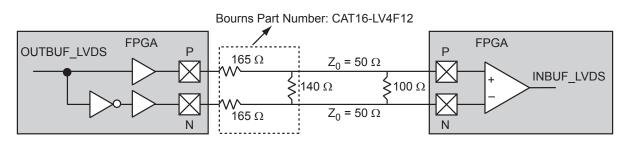


Figure 2-23 • LVDS Circuit Diagram and Board-Level Implementation

1.2 V DC Core Voltage

Table 2-124 • Input Data Register Propagation DelaysCommercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t _{ICLKQ}	Clock-to-Q of the Input Data Register	0.68	ns
t _{ISUD}	Data Setup Time for the Input Data Register	0.97	ns
t _{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t _{ISUE}	Enable Setup Time for the Input Data Register	1.02	ns
t _{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t _{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	1.19	ns
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	1.19	ns
t _{IREMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t _{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t _{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t _{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t _{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
t _{ICKMPWH}	Clock Minimum Pulse Width HIGH for the Input Data Register	0.31	ns
t _{ICKMPWL}	Clock Minimum Pulse Width LOW for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

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IGLOOe DC and Switching Characteristics

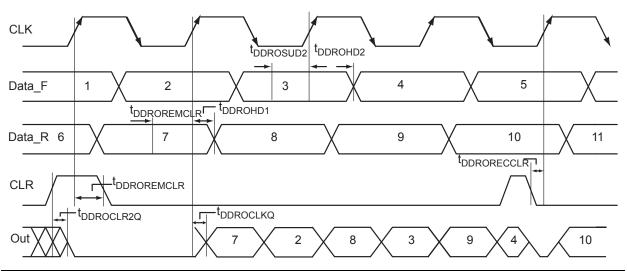


Figure 2-34 • Output DDR Timing Diagram

VersaTile Specifications as a Sequential Module

The IGLOOe library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *IGLOO*, *Fusion*, *and ProASIC3 Macro Library Guide*.

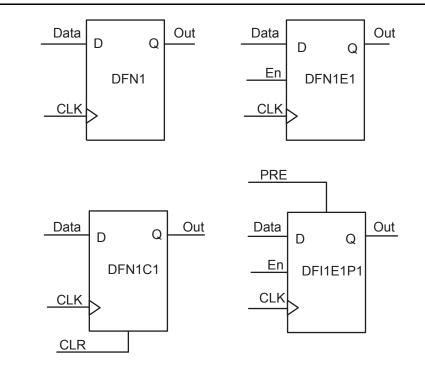


Figure 2-37 • Sample of Sequential Cells



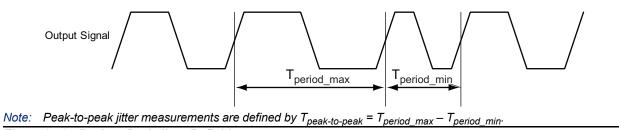


Figure 2-40 • Peak-to-Peak Jitter Definition

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IGLOOe DC and Switching Characteristics

FIFO

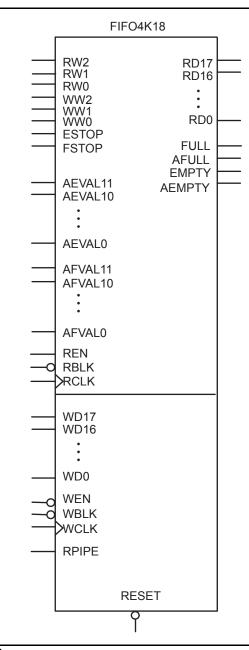


Figure 2-47 • FIFO Model

User Pins

I/O

GL

FF

User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to VCCI. With VCCI, VMV, and VCC supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *IGLOOe FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure section of the IGLOOe FPGA Fabric User's Guide for an explanation of the naming of global pins.

Flash*Freeze Mode Activation Pin

Flash*Freeze mode is available on IGLOOe devices. The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O. The FF pin can be configured as a Schmitt trigger input.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.



FG896			FG896	FG896			
Pin Number	AGLE3000 Function	Pin Number	AGLE3000 Function	Pin Number	AGLE3000 Function		
A2	GND	AA8	IO245NDB6V1	AB13	IO206PDB5V1		
A3	GND	AA9	GEB1/IO235PPB6V0	AB14	IO198NDB5V0		
A4	IO14NPB0V1	AA10	VCC	AB15	IO198PDB5V0		
A5	GND	AA11	IO226PPB5V4	AB16	IO192NDB4V4		
A6	IO07NPB0V0	AA12	VCCIB5	AB17	IO192PDB4V4		
A7	GND	AA13	VCCIB5	AB18	IO178NDB4V3		
A8	IO09NDB0V1	AA14	VCCIB5	AB19	IO178PDB4V3		
A9	IO17NDB0V2	AA15	VCCIB5	AB20	IO174NDB4V2		
A10	IO17PDB0V2	AA16	VCCIB4	AB21	IO162NPB4V1		
A11	IO21NDB0V2	AA17	VCCIB4	AB22	VCC		
A12	IO21PDB0V2	AA18	VCCIB4	AB23	VCCPLD		
A13	IO33NDB0V4	AA19	VCCIB4	AB24	VCCIB3		
A14	IO33PDB0V4	AA20	IO174PDB4V2	AB25	IO150PDB3V4		
A15	IO35NDB0V4	AA21	VCC	AB26	IO148PDB3V4		
A16	IO35PDB0V4	AA22	IO142NPB3V3	AB27	IO147NDB3V4		
A17	IO41NDB1V0	AA23	IO144NDB3V3	AB28	IO145PDB3V3		
A18	IO43NDB1V0	AA24	IO144PDB3V3	AB29	IO143PDB3V3		
A19	IO43PDB1V0	AA25	IO146NDB3V4	AB30	IO137PDB3V2		
A20	IO45NDB1V0	AA26	IO146PDB3V4	AC1	IO254PDB6V2		
A21	IO45PDB1V0	AA27	IO147PDB3V4	AC2	IO254NDB6V2		
A22	IO57NDB1V2	AA28	IO139NDB3V3	AC3	IO240PDB6V0		
A23	IO57PDB1V2	AA29	IO139PDB3V3	AC4	GEC1/IO236PDB6V0		
A24	GND	AA30	IO133NDB3V2	AC5	IO237PDB6V0		
A25	IO69PPB1V3	AB1	IO256NDB6V2	AC6	IO237NDB6V0		
A26	GND	AB2	IO244PDB6V1	AC7	VCOMPLE		
A27	GBC1/IO79PPB1V4	AB3	IO244NDB6V1	AC8	GND		
A28	GND	AB4	IO241PDB6V0	AC9	IO226NPB5V4		
A29	GND	AB5	IO241NDB6V0	AC10	IO222NDB5V3		
AA1	IO256PDB6V2	AB6	IO243NPB6V1	AC11	IO216NPB5V2		
AA2	IO248PDB6V1	AB7	VCCIB6	AC12	IO210NPB5V2		
AA3	IO248NDB6V1	AB8	VCCPLE	AC13	IO204NDB5V1		
AA4	IO246NDB6V1	AB9	VCC	AC14	IO204PDB5V1		
AA5	GEA1/IO234PDB6V0	AB10	IO222PDB5V3	AC15	IO194NDB5V0		
AA6	GEA0/IO234NDB6V0	AB11	IO218PPB5V3	AC16	IO188NDB4V4		
AA7	IO243PPB6V1	AB12	IO206NDB5V1	AC17	IO188PDB4V4		



Revision	Changes	Page
Revision 9 (continued)	The example in the paragraph above Table 2-31 • Duration of Short Circuit Event before Failure was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 32287).	2-31
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is $\pm 100 \mu$ A. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34766).	2-23, 2-35, 2-48
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34886).	2-32
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 34793): "It uses a 5 V-tolerant input buffer and push-pull output buffer."	2-38
	Table 2-143 • IGLOOe CCC/PLL Specification and Table 2-144 • IGLOOe CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34818).	2-91, 2-92
	The following figures were deleted. Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 34869).	
	Figure 2-46 • Write Access after Write onto Same Address	
	Figure 2-47 • Read Access after Write onto Same Address	
	Figure 2-48 • Write Access after Read onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-50 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35749).	2-95, 2-98, 2-104, 2-106
	The "Pin Descriptions and Packaging" chapter is new (SAR 34768).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34768)	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOOe Device Status" table on page II indicates the status for each device in the device family.	N/A



Revision	Changes	Page
Revision 6 (Feb 2009) Product Brief v1.3	The "Pro (Professional) I/O" section was revised to add two bullets regarding wide range power supply voltage support.	Ι
	3.0 V was added to the list of supported voltages in the "Pro I/Os with Advanced I/O Standards" section. The "Wide Range I/O Support" section is new.	1-7
Revision 5 (Oct 2008) Product Brief v1.2	The Quiescent Current values in Table 1 • IGLOOe Product Family table were updated.	I
Revision 4 (Jul 2008) Product Brief v1.1 DC and Switching Characteristics Advance v0.3	As a result of the Libero IDE v8.4 release, Actel now offers a wide range of core voltage support. The document was updated to change $1.2 \text{ V} / 1.5 \text{ V}$ to 1.2 V to 1.5 V .	N/A
Revision 3 (Jun 2008) DC and Switching Characteristics Advance v0.2	Tables have been updated to reflect default values in the software. The default I/O capacitance is 5 pF. Tables have been updated to include the LVCMOS 1.2 V I/O set. DDR Tables have two additional data points added to reflect both edges for Input DDR setup and hold time. The power data table has been updated to match SmartPower data rather then	N/A
	simulation values. Table 2-144 • IGLOOe CCC/PLL Specification was updated to add VMV to the VCCI parameter row and remove the word "output" from the parameter description for VCCI. Table note 3 was added.	2-92
	Table 2-2 • Recommended Operating Conditions 1 was updated to include the T _J parameter. Table note 9 is new.	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature1, the maximum operating junction temperature was changed from 110° to 100°.	2-3
	VMV was removed from Table 2-4 • Overshoot and Undershoot Limits 1, 3. The title of the table was revised to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	Figure 2-2 • V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels is new.	2-5
	EQ 2 was updated. The temperature was changed to 100°C, and therefore the end result changed.	2-6
	The table notes for Table 2-9 • Quiescent Supply Current (IDD), IGLOOe Flash*Freeze Mode*, Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOOe Sleep Mode*, and Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOOe Shutdown Mode* were updated to remove VMV and include PDC6 and PDC7. VCCI and VJTAG were removed from the statement about IDD in the table note for Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOOe Shutdown Mode*.	2-7
	Note 2 of Table 2-12 • Quiescent Supply Current (IDD) Characteristics, No Flash*Freeze Mode1 was updated to include VCCPLL. Note 4 was updated to include PDC6 and PDC7.	2-8
	Table note 3 was added to Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and referenced for 1.2 V LVCMOS.	2-9